ELECTRONICS, INC.
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NTE30130
Infrared Emitting Diode for Remote Control and Night Vision Applications 8mm Type Package

Features:
- High Reliability
- Low–Voltage Characteristics
- Narrow Viewing Angle
- Gallium Aluminum Arsenide
- Water Clear Lens

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

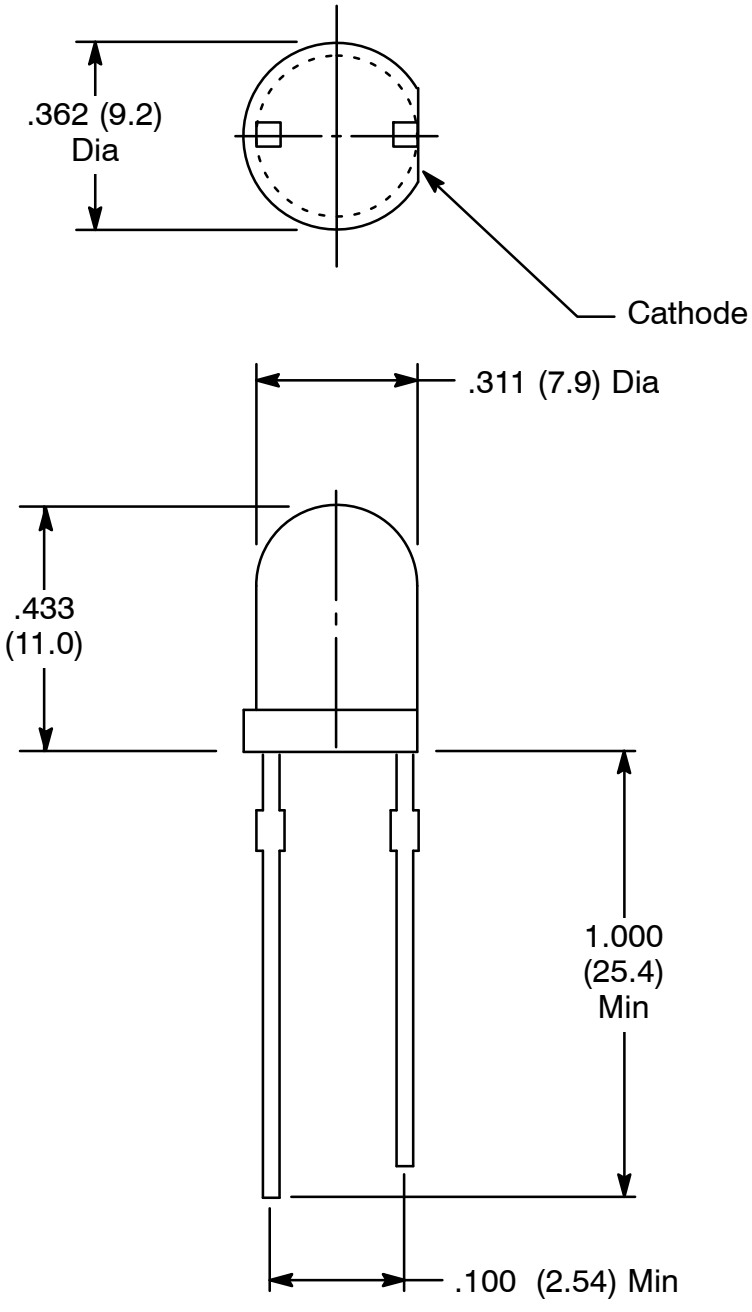
Power Dissipation (Per Chip), P_D 150mW
Reverse Voltage (Per Chip), V_R 5V
Forward Current (Per Chip), I_F
Continuous 100mA
Peak (F = 1kHz, Duty Ratio = 0.1%) 1A
Operating Temperature Range, T_{opr} . . . . . –25° to +85°C
Storage Temperature Range, T_{stg} . . . . . –25° to +85°C

Note 1. IFP Condition: Pulse Width ≤ 10ms, Duty Cycle = 10%.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F = 20mA	1.1	–	1.4	V
		I_F = 100mA	–	1.3	1.6	V
Reverse Current	I_R	V_R = 5V	–	–	10	μA
Peak Emission Wavelength	λ_p	I_F = 20mA	–	940	–	nm
Half Intensity Angle	$2\theta 1/2$	I_F = 20mA	–	50	–	degree
Radiant Intensity	I_E	I_F = 20mA	–	15	–	mw/sr
		I_F = 100mA	–	60	–	mw/sr
Junction Capacity	C_j	V_R = 0V, f = 1MHz	–	50	–	pF
Rise/Fall Time	t_r/t_f	I_{FP} = 100mA, f = 1kHz, t_p/T = 1%	–	1	–	ns

RoHS 2002/95/EC


.362 (9.2)
Dia
Cathode
.311 (7.9) Dia
.433
(11.0)
1.000
(25.4)
Min
.100 (2.54) Min